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600 V power Schottky silicon carbide diode

Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- Dedicated to PFC boost diode

Description

The SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide bandgap material allows the design of a Schottky diode structure with a 600 V rating. Due to the Schottky construction no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

ST SiC diodes will boost the performance of PFC operations in hard switching conditions.

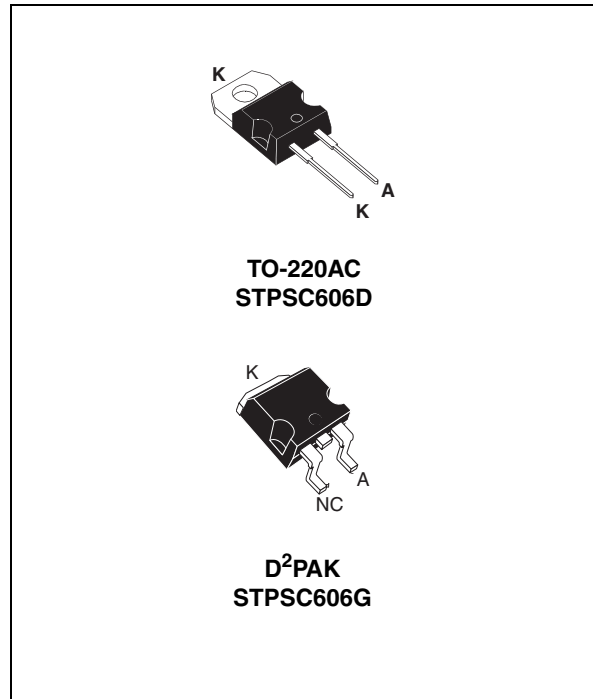


Table 1. Device summary

$I_{F(AV)}$	6 A
V_{RRM}	600 V
$T_J (max)$	175 °C
$Q_C (typ)$	6 nC

1 Characteristics

Table 2. Absolute ratings (limiting values at 25 °C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		600	V
$I_{F(RMS)}$	Forward rms current		18	A
$I_{F(AV)}$	Average forward current	$T_c = 125\text{ °C}, \delta = 0.5$	6	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms sinusoidal}, T_c = 25\text{ °C}$	27	A
		$t_p = 10\text{ ms sinusoidal}, T_c = 125\text{ °C}$	22	
		$t_p = 10\text{ }\mu\text{s square}, T_c = 25\text{ °C}$	110	
I_{FRM}	Repetitive peak forward current	$\delta = 0.1, T_c = 110\text{ °C}, T_j = 150\text{ °C}$	27	A
T_{stg}	Storage temperature range		-55 to +175	°C
T_j	Operating junction temperature range		-40 to +175	°C

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	2.8	°C/W

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$	-	15	75	μA
		$T_j = 150\text{ °C}$		-	100	750	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 6\text{ A}$	-	1.4	1.7	V
		$T_j = 150\text{ °C}$		-	1.6	2.1	

1. $t_p = 10\text{ ms}, \delta < 2\%$

2. $t_p = 500\text{ }\mu\text{s}, \delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 1.20 \times I_{F(AV)} + 0.15 \times I_{F(RMS)}^2$$

Table 5. Other parameters

Symbol	Parameter	Test conditions	Typ.	Unit
Q_c	Total capacitive charge	$V_r = 400\text{ V}, I_F = 6\text{ A}, di_F/dt = -200\text{ A}/\mu\text{s}$ $T_j = 150\text{ °C}$	6	nC
C	Total capacitance	$V_r = 0\text{ V}, T_c = 25\text{ °C}, F = 1\text{ Mhz}$	375	pF
		$V_r = 400\text{ V}, T_c = 25\text{ °C}, F = 1\text{ Mhz}$	30	

Figure 1. Forward voltage drop versus forward current (typical values)

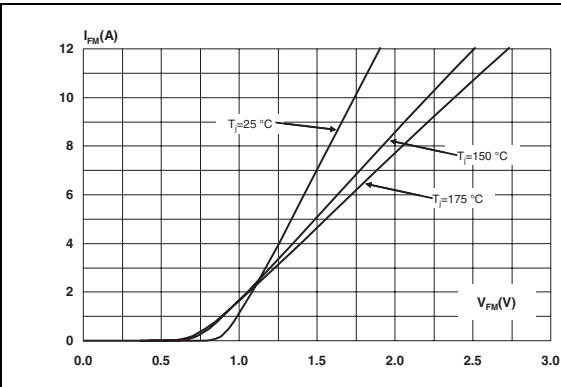


Figure 2. Reverse leakage current versus reverse voltage applied (maximum values)

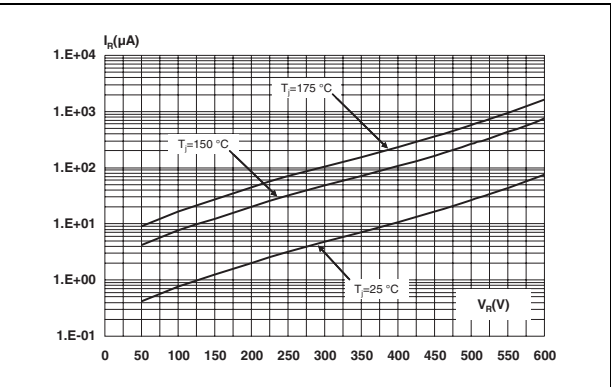


Figure 3. Peak forward current versus case temperature

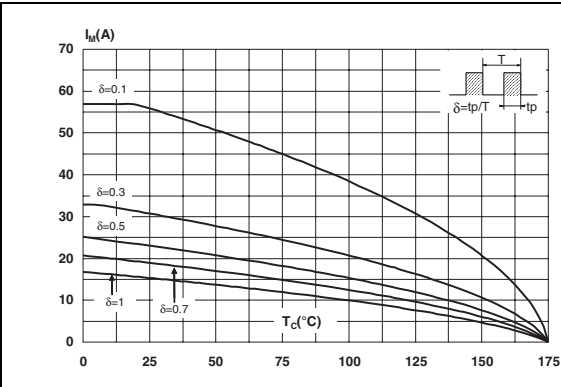


Figure 4. Junction capacitance versus reverse voltage applied (typical values)

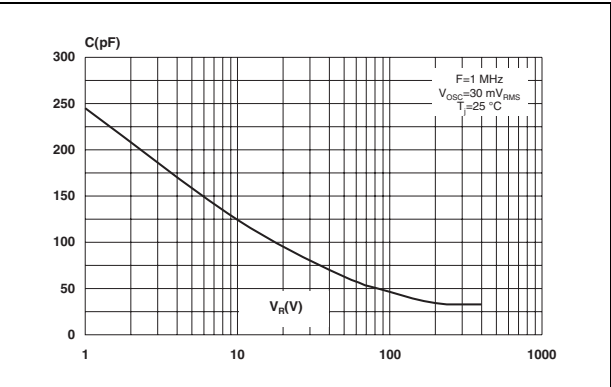


Figure 5. Relative variation of thermal impedance junction to case versus pulse duration

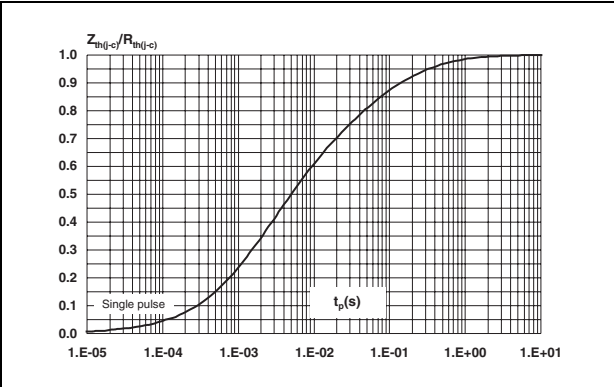


Figure 6. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)

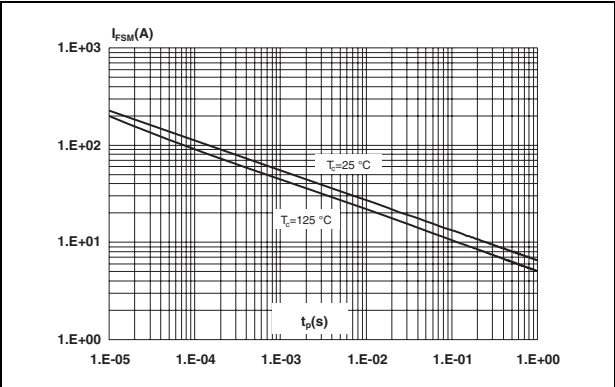
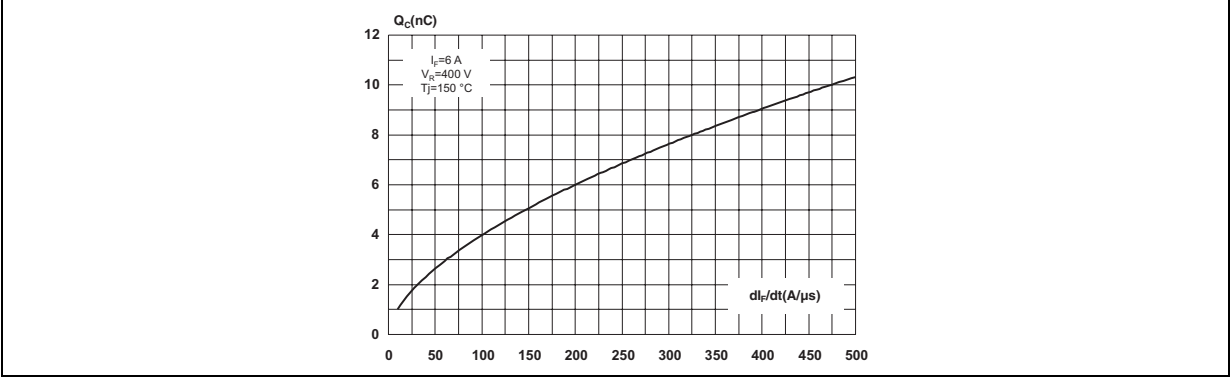


Figure 7. Total capacitive charges versus di_F/dt (typical values)



2 Package information

- Epoxy meets UL94, V0
- Cooling method: convection (C)
- Recommended torque: 0.4 to 0.6 N·m

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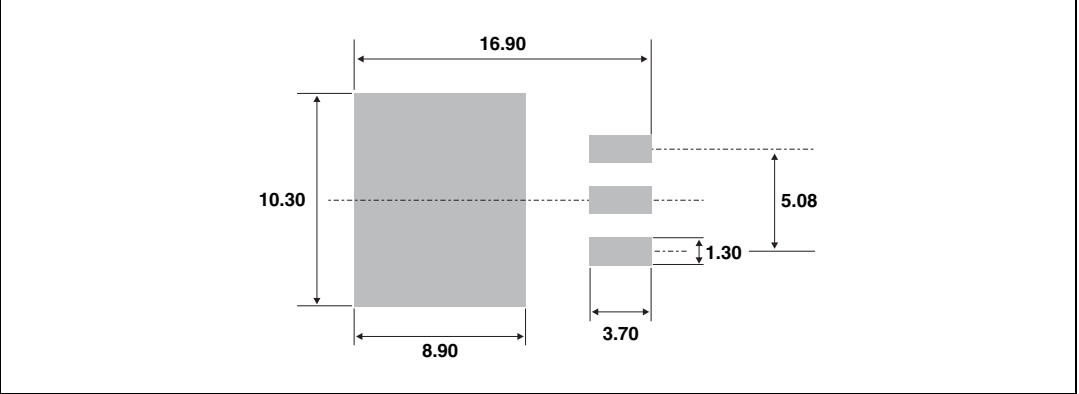
Table 6. TO-220AC dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
H2	10.00	10.40	0.393	0.409
L2	16.40 typ.		0.645 typ.	
L4	13.00	14.00	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam. I	3.75	3.85	0.147	0.151

Table 7. D²PAK dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
B	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
C	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
E	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
M	2.40	3.20	0.094	0.126
R	0.40 typ.		0.016 typ.	
V2	0°	8°	0°	8°

Figure 8. Footprint (dimensions in mm)



3 Ordering information

Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPSC606D	STPSC606D	TO-220AC	1.86 g	50	Tube
STPSC606G-TR	STPSC606G	D ² PAK	1.48 g	1000	Tape and reel

4 Revision history

Table 9. Document revision history

Date	Revision	Changes
24-Sep-2009	1	First issue.

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